

PTO/SB/08A(10-01)
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Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number. Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE 10/054601 **Application Number** STATEMENT BY APPLICANT Filing Date January 22, 2002 many sheets as necessary) Forbes, Leonard **First Named Inventor Group Art Unit** 2879 Santiago, Mariceli **Examiner Name** Attorney Docket No: 303.504US3

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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Examiner	Cite	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s),	T²		
Initials*	No'	publisher, city and/or country where published.			

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	Sheet 1 of 2
Atty. Docket No.: 303.504US3	Serial No. Unknown
Applicant: Leonard Forbes et al.	.s. 1601 1601
Filing Date: Herewith	Group: Unknown

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Joseph Williams

*Substitute Disclosure Statement Form (PTO-1449)

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Form 1449*	Atty. Docket No.: 303.504US3	Serial No. Unknown 10/0546	
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